MICRO ELECTRONICS

2N3962

PNP SILICON TRANSISTOR

TO-18

CBE

DESCRIPTION

2N3962 is PNP silicon planar transistor designed for AF small signal amplifier stages.

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCEO	60V
Collector-Base Voltage	VCBO	60V
Emitter-Base Voltage	VEBO	6V
Collector Current	IC	200mA
Continuous Power Dissipation	Pd	360mW
Operating & Storage Junction Temperature	Tj,Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LVCEO	60		V	IC=5mA	IB=0
Collector-Base Breakdown Voltage	BVCBO	60		V	IC=10μA	IE=0
Emtter-Base Breakdown Voltage	BVEBO	6		V	IE=10μA	IC=0
Collector Cutoff Current	ICES		10	nA	VCE=50V	VEB=0
Emitter Cutoff Current	IEBO		10	nA	VEB=4V	IC=0
D.C. Current Gain	HFE	60			IC=0.001mA	VCE=5V
		100	300		IC=0.01mA	VCE=5V
		100	450		IC=1mA	VCE=5V
		90			IC=50mA	VCE=5V
Collector-Emitter Saturation Voltage	VCE(sat)		0.25	V	IC=10mA	IB=0.5mA
			0.4	V	IC=50mA	IB=5mA
Base-Emitter Saturation Voltage	VBE(sat)		0.95	V	IC=50mA	IB=5mA
Output Capacitance	Cob		6	pF	VCB=10V	f=1MHz
Noise Figure	NF		3	dB	IC=0.02mA	VCE=5V
					REB=10Kohm	f=1kHz

* Pulse test : pulse width <300μS, duty cycle < 2%.

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